

Application No. 10/711,841
Technology Center 2827
Reply dated November 26, 2007
In Response to Office Action dated August 31, 2007

REMARKS

As of the filing of the present reply, claims 1, 3-5, 7-21, 23-28, and 30 were pending in the above-identified US Patent Application. In the immediately preceding Office Action, the Examiner allowed claims 1, 3-5, 7, 8, 11-21, 23-28, and 30, but rejected independent claim 9 and its dependent claim 10. Under this rejection, the Examiner explained that claims 9 and 10 were anticipated under 35 USC §102(e) by U.S. Published Patent Application No. 2003/0126356 to Gustavson et al. (Gustavson) because Gustavson discloses a "nonvolatile memory device," in particular a "flash memory device," with multiple pages open in a block or sector thereof and latches coupled to a sense amplifier and operating in the storage of data read-from and written-to the sense amplifier to keep multiple pages open.

Gustavson discloses a memory system having Synchronous-Link DRAM (SLDRAM), and focuses on how multiple modules of DRAM can be combined into one memory subsystem using a synchronous link. As well known in the art, DRAM (Dynamic Random Access Memory) is the most common form of volatile memory and comprises one capacitor and one gate transistor per memory cell. The fact that the capacitors will leak charge over time makes DRAM data retention dependent on periodic refresh cycles, during

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which data are read from the memory cells and then written back (restored) to the same cells. Without this refresh, data are lost from DRAM and since the refresh depends on the availability of power, any interruption of power will result in instantaneous loss of data. This volatility of data is in contrast to what is referred to as "nonvolatile" memory, such as flash or EEPROMs, which retain data even after interruption of the supply power. Thus, Gustavson's SLD RAM system is a volatile memory device, and not Applicants' claimed "nonvolatile memory device," and particularly not Applicants' claimed "flash memory device."

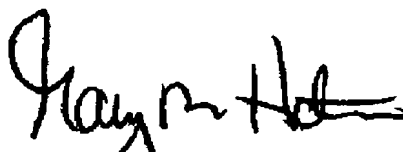
Though the rejection of claims 9 and 10 was explained on the basis that Gustavson discloses a "flash memory device" with all of the features recited in claims 9 and 10, Applicants have searched but are unable to find any reference to Gustavson's SLD RAM being nonvolatile memory and used as a data storage device. The only reference to any nonvolatile memory device in Gustavson is at paragraph [0137] regarding the data sheet of each module being stored within the entire system of SLD RAM, namely, in the form of local configuration memory (LCM) that has information regarding the physical and electrical organization of each memory module and are typically programmed during production of the modules. This reference in Gustavson

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to nonvolatile memory is very different from the use of nonvolatile memory as data storage media, as required by Applicants' claims 9 and 10. Applicants therefore respectfully request withdrawal of the rejection of claims 9 and 10 under 35 USC §102.

Should the Examiner have any questions with respect to any matter now of record, Applicants' representative may be reached at (219) 462-4999.

Respectfully submitted,



Gary M. Hartman
Reg. No. 38,898

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Hartman & Hartman, P.C.
Valparaiso, Indiana 46383
TEL.: (219) 462-4999
FAX: (219) 464-1166